



# 제 29회 한국반도체학술대회

The 29th Korean Conference on Semiconductors

2022년 1월 24일(월)~ 26일(수) | 강원도 하이원 그랜드호텔(컨벤션타워)

2022년 1월 25일(화), 10:45-12:30

Room A (에메랄드 1, 5층)

## D. Thin Film Process Technology 분과 [TA2-D] Memory Devices

좌장: 윤성민 교수(경희대학교), 최창환 교수(한양대학교)

<p><b>TA2-D-1</b> 10:45-11:00</p>	<p><b>Characterization of Charge-Trap Memory Thin-Films Transistors Using Engineered Al-Doped HfO<sub>2</sub> Charge-Trap Layers</b> Jin-Ju Kim and Sung-Min Yoon <i>Department of Advanced Material Engineering for Information and Electronics, Kyung Hee University</i></p>
<p><b>TA2-D-2</b> 11:00-11:30</p>	<p><b>Low Temperature Ferroelectric Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> Thin Films for Future Electronic Device Applications</b> Si Joon Kim <i>Kangwon National University</i></p>
<p><b>TA2-D-3</b> 11:30-11:45</p>	<p><b>Atomic Layer Deposition of SrTiO<sub>3</sub>/BaTiO<sub>3</sub> Thin Films for DRAM Capacitor Applications</b> Jae Deock Jeon<sup>1,2</sup>, Heung-Yoon Choi<sup>1,2</sup>, Seo Young Jang<sup>1,2</sup>, Ju Young Sung<sup>1,2</sup>, Hye Min Lee<sup>1,2</sup>, Wangu Kang<sup>3</sup>, Jeong Hwan Han<sup>3</sup>, and Sang Woon Lee<sup>1,2</sup> <sup>1</sup><i>Department of Energy Systems Research, Ajou University</i>, <sup>2</sup><i>Department of Physics, Ajou University</i>, <sup>3</sup><i>Department of Materials Science and Engineering, Seoul National University of Science and Technology</i></p>
<p><b>TA2-D-4</b> 11:45-12:00</p>	<p><b>Noise Perspective of Top Gate Last Processed IGZO Devices with Oxygen Tunnel Structure</b> Y. Yoon<sup>1</sup>, S. Subhechha<sup>2</sup>, E. Simoen<sup>2</sup>, R. Delhougne<sup>2</sup>, and G. S. Kar<sup>2</sup> <sup>1</sup><i>SK Hynix</i>, <sup>2</sup><i>IMEC</i></p>
<p><b>TA2-D-5</b> 12:00-12:15</p>	<p><b>The Effect of Post-depositing Annealing on the Electrical Properties ZrO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub>/ZrO<sub>2</sub> Thin Films</b> Jinseok Hwang and Il-Kwon Oh <i>Department of Electrical and Computer Engineering, Ajou University</i></p>
<p><b>TA2-D-6</b> 12:15-12:30</p>	<p><b>Enhanced Electrical Properties of Al-Doped TiO<sub>2</sub> Capacitor Dielectric Film on the TiN Electrode by Adopting Atomic Layer Deposited Ru Interlayer</b> Dae Seon Kwon, Tae Kyun Kim, Junil Lim, Haengha Seo, Heewon Paik, and Cheol Seong Hwang <i>Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University</i></p>